

# MICROWAVE POWER GaAs FET

TIM0910-30L

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 45.0dBm at 9.5GHz to 10.5GHz

·HIGH GAIN

G1dB= 7.0dB at 9.5GHz to 10.5GHz

**LOW INTERMODULATION DISTORTION** 

IM3(Min)= -25dBc at Po= 38.0dBm Single Carrier Level

·HERMETICALLY SEALED PACKAGE



## RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 7.0A f = 9.5 to 10.5GHz	dBm	44.0	45.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.0	7.0	_
Drain Current	IDS1		Α		10.0	11.5
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%		25	_
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 38.0dBm, Δf= 5MHz (Single Carrier Level)	dBc	-25		_
Drain Current	IDS2		Α	_	9.0	10.1
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_		100

Recommended Gate Resistance (Rg): 10  $\Omega$ 

### **ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 9.6A	S	_	5.5	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 290mA	V	-0.7	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	20.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -290 <sub>μ</sub> A	٧	-5	_	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.0	1.1

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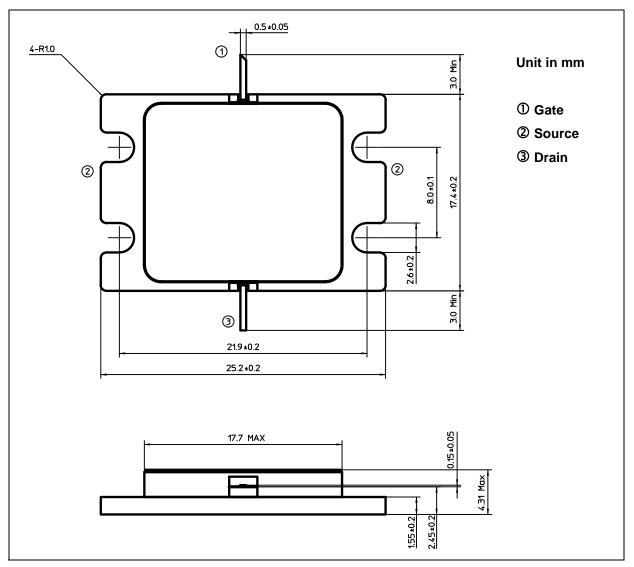


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## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25 °C)	PT	W	136
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

# **PACKAGE OUTLINE (7-AA03A)**



### HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.